

1.19.2

Form vertical stack of semiconductor layers for a bipolar transistor Etch away lateral portion of top most one of the layers to expose portion of the base layer Form a dielectric sidewall around the remainder of the top most one of the layers Grow semiconductor on the exposed portion of the base layer to laterally surround part of the top most one of the layers Fig. 3

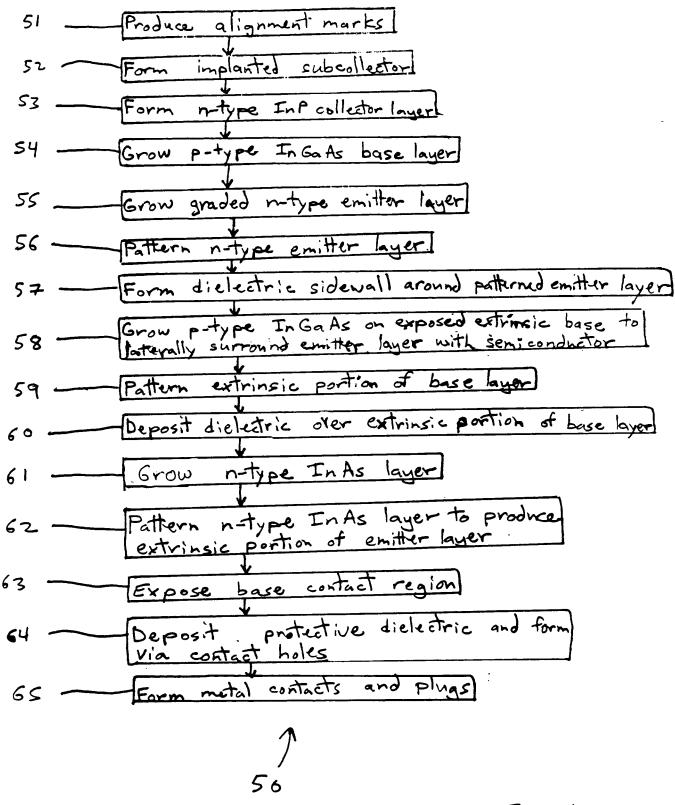
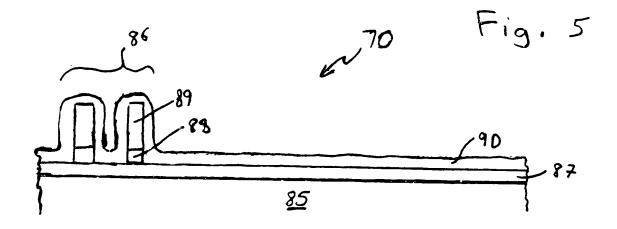
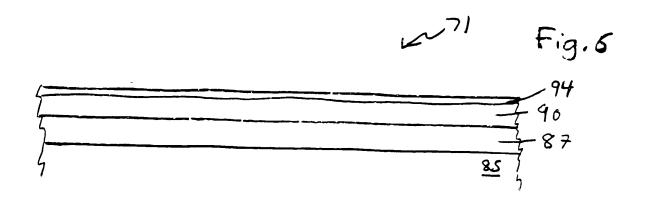


Fig. 4





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